PTO/SB/08A (08-00)

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Under the Paperwork Reduction Act of 1995, no persons are to respond to ection of information unless it contains a valid OMB control number. ROOM Complete if Known Substitute for form 1449A/PTO 10/712,062 INFORMATION DISCLOSURE Application Number November 14, 2003 Filing Date STATEMENT BY APPLICANT Shunpei YAMAZAKI et al. First Named Inventor (use as many sheets as necessary) 2826 Group Art Unit F. Abraham Examiner Name Attorney Docket Number Sheet 0756-7218

				U.S. PATENT DOCUMENT	rs	
Examiner Initials	Cite No.1	U.S. Patent Document		Name of Patentee or Applicant of Cited	Date of Publication of Cited Document MM-DD-YYYY	Pages, Cohmans, Lines, Where Relevant Passages or Relevant Figures Appear
			ind Code ² (known)	Document		
TA		5,531,862		Otsubo et al.	07/02/1996	
		5,575,883		Nishikawa	11/19/1996	
		5,902,993		Okushiba et al.	05/11/1999	
		6,006,763		Mori et al.	12/28/1999	
V		4,086,020		Tanabe et al.	04/25/1978	
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Examiner Initials	Cite No.1			Name of Patentee or	Date of Publication of Cited Document	Relevant Passages or Relevant		
		Office	Number ⁴	(if known)	Applicant of Cited Document	MM-DD-YYYY	Figures Appear	T*
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^{*}EXAMINER! Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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PTO/SB/08A (08-00)

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Substitute	for form 1449A/PTO			Complete if Known		
MARTIN	RMATION I	NISC	LOSURE	Application Number	10/712,062	
	EMENT BY			Filing Date	November 14, 2003	
SIAI				First Named Inventor	Shunpei YAMAZAKI et al.	
	(use as many sheets a	as necessi	(ציי	Group Art Unit	2826	
				Examiner Name	F. Abraham	
Sheet	ı	of	1	Attorney Docket Number	0756-7218	

				U.S. PATENT DOCUMEN	TS	
Examiner Initials	Cite No. ¹	U.S. Patent (Document	Name of Patentee or Applicant of Cited	Date of Publication of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
D.		Number	Kind Code ² (if known)	Document	MM-DD-YYYY	
1,8		5,970,327		Makita et al	10/19/1999	
		6,177,302	Ì	Yamazaki et al.	01/23/2001	
		6,465,287		Yamazaki et al.	10/15/2002	
		6,482,686		Takemura	11/19/2002	(
		6,495,404		Teramoto et al.	12/17/2002	
		6,528,358		Yamazaki et al.	03/04/2003)
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		Office	Number ⁴	Kind Code ³ (if known)	Applicant of Cited Document	MM-DD-YYYY	Figures Appear	τ•
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Substitut	e for form 1449A/PTO			Complete if Known		
INFO	RMATION I	DISC	LOSURE	Application Number	Based on 10/214,691	
INFORMATION DISCLOSURE				Filing Date	August 9, 2002	
SIA	STATEMENT BY APPLICANT			First Named Inventor	Shunpei YAMAZAKI, et al.	
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				Examiner Name	Fetsum Abraham	
Sheet 1 of 12			12	Attorney Docket Number	0756-7218	

			U.S. PATENT DOCUMENT	rs	
Examiner Initials	Cite No. 1	U.S. Patent Document Number Kind Code ((f Inorn)	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
PP		5,686,328	Zhang et al.	11/11/97	0
		5,763,899	Yamazaki et al.	06/09/98	
		5,782,665	Weisfield et al.	07/21/98	/
		5,922,125	Zhang	07/13/99	
		6,083,801	Ohtani	07/04/00	
		5,744,822	Takayama et al.	04/28/98	
		5,744,824	Kousai et al.	04/28/98)
		5,766,977	Yamazaki	06/16/98	
		5,773,846	Zhang et al.	06/30/98	/
		5,773,847	Hayakawa	06/30/98	(
		5,773,327	Yamazaki et al.	06/30/98	
		5,795,795	Kousai et al.	08/18/98	
		5,808,321	Mitanaga et al.	09/15/98)
		3,890,632	Ham et al.	06/17/75	
		4,330,363	Biefesen et al.	05/18/82	
	-	4,466,073	Boyan et al.	08/14/84	
	- 3.	5,543,636	Yamazaki	08/06/96	
		6,140,165	Zhang et al.	10/31/00	
		6,147,667	Yamazaki et al.	11/14/00	
	-	6,180,439 B1	Yamazaki et al.	01/30/01	
		5,929,527	Yamazaki et al.	07/27/99	
		5,949,107	Zhang	09/07/99	
		6,031,249	Yamazaki et al.	02/29/00	
		6,121,683	Yamazaki et al.	09/19/00	
		6,207,969 B1	Yamazaki et al:	03/27/01	

		OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS	
Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T²
		Japan J. Appl. Phys. 8 (1969) 1056, "Effect of Deposited Metals on the Crystallization Temperature of Amorphous Germanium Film," OKI et al.	
		Technology Information Association, "Thermo-Auto-Chrome Full Color Recording Technology," May 31, 1995	

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				Examiner Name	Fetsum Abraham	
Sheet 2 of 12			12	Attorney Docket Number	0756-7218	

			U.S. PATENT DOCUMEN	TS	
Examiner Initials	Cite No. ¹	U.S. Patent Document Number Kind Code ² ((f known)	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columna, Lines, Where Relevant Passages or Relevant Figures Appear
PR		5,811,327	Funai et al.	09/22/98	
		5,818,076	Zhang et al.	10/06/98	
		5,821,138	Yamazaki et al.	10/13/98	
		5,824,574	Yamazaki et al.	10/20/98	
		6,175,348	Zhang et al.	01/16/01	
		5,728,259	Suzawa et al.	03/17/98	
		6,278,132 B1	Yamazaki et al.	08/21/01	
		5,818,076	Zhang et al.	10/06/98	
		3,389,024	Schimmer	06/18/68	
		3,783,049	Sandera.	01/01/74	
,		4,059,461	Fan et al.	11/22/77	
		4,068,020	Reuschel	01/10/78	
		4,132,571	Cuomo et al.	01/02/79	
		4,174,217	Flatley	11/13/79	
		4,226,898	Ovshinsky et al.	10/07/80	
		4,231,809	Schmidt	11/04/80	
}		4,271,422	Ipri	06/02/81	
		4,277,884	Hsu	07/14/81	
		4,300,989	Chang	11/17/81	
		4,309,224	Shibata	01/05/82	
		4,331,709	Risch et al.	05/25/82	/
		4,379,020	Glaeser et al.	04/05/83	
ı		4,409,724	Tasch, Jr., et al.	10/18/83	
		4,472,458	Sirinyan et al.	09/18/84	
		4,481,121	Barthel	11/06/84	
		4,534,820	Mori et al.	08/13/85	
		4,544,418	Gibbons	10/01/85	

				F	OREIGN PATENT DOC	UMENTS		
Examiner Cite Initials No.	Foreign Patent Document			Name of Patentee or	Date of Publication of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant		
),	Office ³ Number ⁴ ((f known)	Kind Code ³ (if known)	Applicant of Cited Document	MM-DD-YYYY	Figures Appear	T*		
		JP	07-335900)	Teramoto Satoshi	12/22/95		Abst.
		JP	64-081324			03/27/89		Abst.
			от	HER PRIOR	ART - NON PATENT LITE	RATURE DOCUMENTS		
Examiner Initials	Cite No.		Include na item (bool	ame of the auth	nor (in CAPITAL LETTERS), nurnal, serial, symposium, catal publisher, city and/or coun	og, etc.)., date, page(s), volum	priate), title of the e-issue number(s),	T²
Par	,	ВМ	Technical	Disclosure	Bulletin, Vol. 11, No	o.7, A.R. Baker, Jr.		
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B/	1	4,546,376	Nakata et al.	10/08/85	
	 	4,597,160	Ipri	07/01/86	/
		4,634,473	Swartz et al.	01/06/87	/
	 	4,735,824	Yamabe et al.	04/05/88	
		4,755,481	Faraone	07/05/88	
	†	4,911,781	Fox et al.	03/27/90	
	<u> </u>	4,959,247	Moser et al.	09/25/90	
		4,959,700	Yamazaki	09/25/90	
	 	4,996,077	Mosiehi et al.	02/26/91	
	İ	4,996,523	Bell et al.	02/26/91	\
		5,043,224	Jaccodine et al.	08/27/91	,
		5,075,259	Moran	12/24/91	
	1	5,089,441	Mosiehi	02/18/92	/
		5,112,764	Mitra et al.	05/12/92	
	1	5,145,808	Sameshima et al.	09/08/92	/
		5,147,826	Liu et al.	09/15/92	/
		5,173,446	Asakawa et al.	12/22/92	
	·	5,200,630	Nakamura et al.	04/06/93	
		5,221,423	Sugino et al.	06/22/93	
		5,225,355	Sugino et al.	07/06/93	
		5,244,836	Lim	09/14/93	
	Ĭ	5,254,480	Tran	10/19/93	
		5,262,350	Yamazaki et al.	11/16/93	
		5,262,654	Yamazaki	11/16/93	
		5,275,851	Fonash et al.	01/04/94	
		5,278,093	Yonehara	01/11/94	/
		5,289,030	Yamazaki et al.	02/22/94	
		5,296,405	Yamazaki et al.	03/22/94	
		5,298,075	Lagendijk et al.	03/29/94	
		5,308,998	Yamazaki et al.	05/03/94	
		5,313,075	Zhang et al.	05/17/94	
		5,352,291	Zhang et al.	10/04/94	
		5,354,697	Oostra et al.	10/11/94	
	<u> </u>	5,358,907	Wong	10/25/94	
		5,366,926	Mei et al.	11/22/94	
		\$,387,530	Doyle et al.	02/07/95	
4		5,424,230	Wakai	06/13/95	

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SIA			First Named Inventor	Shunpei YAMAZAKI, et al.	
			Group Art Unit	2826	
				Examiner Name	Fetsum Abraham
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r M	Ļ	5,470,763	Hamada	11/28/95	<u></u>
	ļ	5,480,811	Chiang et al.	01/02/96	
		5,504,019	Miyasaka et al.	04/02/96	
		5,508,207	Horai et al.	04/16/96	
		5,531,182	Yonehara	07/02/96	
		5,580,815	Hsu et al.	12/03/96	
		5,621,244	Yamazaki et al.	04/15/97	
		5,661,311	Takemura et al.	08/26/97)
		5,684,317	Hwang	11/04/97	
		5,684,365	Tang et al.	11/04/97	
i		5,693,541	Yamazaki et al.	12/02/97	
		5,696,003	Makita et al.	12/09/97	
1		5,717,224	Zhang	02/10/98	
		5,734,179	Chang et al.	03/31/98	
		5,773,327	Yamazaki et al.	06/30/98	
		5,786,796	Takayama et al.	07/28/98	\
		5,821,560	Arai et al.	10/13/98	
i		5,828,429	Takemura	10/27/98	
i .		5,838,508	Sugawara	11/17/98	/
		5,843,225	Takayama et al.	12/01/98	/
		5,846,857	Ju	12/08/98	
		5,849,611	Yamazaki et al.	12/15/98	
		5,882,960	Zhang et al.	03/16/99	
		5,888,858	Yamazaki et al.	03/30/99	
1		5,895,933	Zhang et al.	04/20/99	
		5,899,547	Yamazaki et al.	05/04/99	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \
		5,929,464	Yamazaki et al.	07/27/99	<u> </u>
1		5,933,205	Yamazaki et al.	08/03/99	
		5,940,732	Zhang	08/17/99	
		5,962,869	Yamazaki et al.	10/05/99	
		5,963,278	Yamazaki et al.	10/05/99	
		5,985,740	Yamazaki et al.	11/16/99	
	-	5,990,491	Zhang	11/23/99	
		5,990,542	Yamazaki	11/23/99	
1,		6,005,648	Zhang et al.	12/21/99	,
- //		6,011,277	Yamazaki	01/04/00	

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Ho		6,013,929		Ohtani	01/11/00	
		6,048,758		Yamazaki et al.	04/11/00	
		6,063,654		Ohtani	05/16/00)
		6,077,731		Yamazaki et al.	06/20/00	
		6,093,934		Yamazaki et al.	07/25/00	
		6,100,562		Yamazaki et al.	08/08/00	
		RE 28,385		Маует	04/08/75	
		RE 28,386		Heiman et al.	04/08/75	

				FC	DREIGN PATENT DOC	UMENTS		
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		EP	0 178 447			10/09/84		English
		JP	01-187814			07/27/89		Full
		JP	01-187874			07/27/89		Abst.
		JP	01-187875			07/27/89		Abst.
		JP	01-206632			08/18/89		Abst.
		JP	02-140915			05/30/90		Full
		JP	02-148687			06/07/90		Abst.
		JP	02-275641			11/09/90		Abst.
		JP	03-280418			12/11/91		Abst.
		JP	03-280420			12/11/91		Full
		JP	05-082442			04/02/93		Abst.
		JP	05-107561			04/30/93		Abst.
		JP	05-299348			11/12/93		Abst.
		JP	06-232059			08/19/94		Full
1		JP	07-161634			06/23/95		Abst.
1	1	JP	07-321339		-	12/08/95		Abst.
		JP	08-129358			05/21/96		Abst.
100		JP	08-129359			05/21/96		Abst.
		JP	08-129360			05/21/96		Abst.
		JP	08-234683			09/13/96		Abst.
	i	JP	08-241047			09/17./96		Abst.
		JР	08-241048			09/17/96	•	Abst.
		JP	08-241057			09/17/96		Abst.
		JP	08-241997			09/17/96		Abst.
		JP	60-105216			06/10/85		Full
		JP	61-063017			04/01/86		Full
T_{-}		JP	61-063107			04/01/86		Abst.
Į		JP	62-169356			07/25/87		Abst.

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				Examiner Name	Fetsum Abraham	
Sheet	6	of	12	Attorney Docket Number	0756-7218	

		OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS								
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.								
Ro		Caune et al., "Combined CW Laser and Furnace Annealing of Amorphous Si and Ge in Contact With Some Metals," January 1, 1989, pp. 597-604, Applied Surface Science, Vol. 36								
		Stoemnos et al., "Crystallization of Amorphous Silicon by Reconstructive Transformation Utilizing Gold," March 18, 1991, pp. 1196-1198, Appl. Phys. Lett. 58(11)								
		Kakkad et al., "Crystallized Si-Films By Low-Temperature Rapid Thermal Annealing of Amorphous Silicon," March 1, 1989, pp. 2069-2072, J. Appl. Phys. 65(5)								
		Oki et al., "Effect of Deposited Metals On The Crystallization Temperature of Amorphous Germanium Film," 1969, pp. 1056, Jpn. J. Appl. Phys. 8	_							
		Kuznetsov et al., "Enhanced Solid Phase Epitaxial Recrystallization of Amorphous Silicon Due to Nickel Silicide Precipitation Resulting From Ion Implantation and Annealing," 1993, pp. 990-993, Nucl. Instruments Methods Physics Research, 880/881								
		Hayashi et al., "Fabrication of Low-Temperature Bottom Gate Poly-Si TFTs on Large Area Substrate by Linear-Beam Excimer Laser Crystallization and Ion Doping Method," January 1, 1995, pp. 829-832, IEEE IEDM								
		Takenaka et al., "High Mobility Poly-Si Thin Film Transistors Using Solid Phase Crystallized a-Si Films Deposited by Plasma Enhanced Chemical Vapor Deposition," December 1990, pp. L2380-L2383, Jpn. J. Appl. Phys. Vol 29, No. 12								
		Hatalis et al., "High Performance Thin-Film Transistors in Low Temperature Crystallized LPCVD Amorphous Silicon Films," August 1987, pp. 361-364, Elec. Dev. Letters Vol. EDL 8, No. 8								
		Zorabedian et al., "Lateral Seeding of Silicon-on-Insulator Using an Elliptical Laser Beam: A Comparison of Scanning Methods," 1984, pp. 81-86, Mat. Res. Soc. Symp. Proc. Vol. 33								
		Green et al., "Method to Purify Semiconductor Wafers," October 1973, pp. 1612-1613, IBM Tech. Discl. Bulletin, Vol. 16, No. 5								
J		Boyd, et al., "Oxidation of Silicon Surfaces by CO2 Lasers," July 15, 1982, pp. 162-164, Applied Phys. Letters, Vol. 41, No. 2								
J		Wolf et al., "Silicon Processing for the VLSI Era Volume 1: Process Technology," 1986, pp. 215-216, Lattice Press								
Examiner	1 .	LA								
Signature		Elw Abraha Date Considered 2/8 D.J								

Approved for use through 10/31/2002. OMB 0651-0031
U.S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

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Complete if Known Substitute for form 1449A/PTO Based on 10/214,691 Application Number INFORMATION DISCLOSURE August 9, 2002 Filing Date STATEMENT BY APPLICANT Shunpei YAMAZAKI, et al. First Named Inventor (use as many sheets as necessary) 2826 Group Art Unit Fetsum Abraham Examiner Name Sheet 7 of 12 Attorney Docket Number 0756-7218

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nitials"	No.	item (book, magazine, journal, serial, symposium, catalog, etc.)., date, page(s), volume-issue number(s), publisher, city and/or country where published.	·
Ro		Lau et al., "Solid Phase Epitaxy in Silicide Forming System," 1977, pp. 313-322, Thin Solid Films, 47	
		Kawazu et al., "Low-Temperature Crystallization of Hydrogenated Amorphous Silicon Induced by Nickel Silicide Formation," December 1990, pp. 2698-2704, Inst. Of Appl. Phys. Vol. 29, No. 12	
		Wolf et al., "Silicon Processing for the VLSI Era Volume 1 – Process Technology," 1986, pp. 550-551, Lattice Press	
	-	Bruines et al., "Between Explosive Crystallization and Amorphous Regrowth: Inhomogeneous Solidification Upon Pulsed Laser Annealing of Amorphous Silicon," March 1, 1987, pp. 507-509, Applied Physics Letter, Vol. 50	
		Kawazu et al., "Initial Stage of the Interfacial Reaction between Nickel and Hydrogenated Amorphous Silicon," April 1, 1990, pp. 729-738, Japanese Journal of Appl. Phys., Vol.29	
		Kakkad et al., "Low Temperature Selective Crystallization of Amorphous Silicon," 1989, pp. 66-68, Journal of Non-Crystalline Solids, 115	
		Suresh et al., "Electroless Plated Nickel Contacts to Hydrogenated Amorphous Silicon," January 1, 1994, pp. 78-81, Thin Solids Films, Vol. 252	
		Sakaguchi et al., "Current Progress in Epitaxial Layer Transfer," March 1, 1997, pp. 378-387, IEICE Trans. Electron, Vol. E80 C/No. 3	
		Kouvatsos et al., "Fluorine-Enhanced Oxidation of Polycrystalline Silicon and Application to Thin-Film Transistor Fabrication," August 24, 1992, pp. 937-939, Appl. Phys. Letter, Vol. 61, No. 8	
		Sze, "VLSI Technology," January 1, 1988, pp. 397-400, McGraw-Hill Publishing Company, Second Edition	
i		Ghandhi, "VLSI Fabrication Principles," January 1, 1983, pp. 419-429, Wiley and Sons	
1		Kuper et al., "Effects of Fluorine Implantation on the Kinetics of Dry Oxidation of Silicon," August 1, 1986, pp. 985-990, J. Applied Physics	
1		Wolf et al., "Silicon Processing for the VLSI Era Volume 1: Process Technology," 1986, pp. 198-207, Lattice Press	

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OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS						
Examiner Initials	Cite No.1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T²			
To		Thompson et al., "Silicide Formation in Pd-a-Si:H Schottky Barriers," August 1981, pp. 274-276, Appl. Phys. Lett., Vol. 39, No. 3				
		Nemanich et al., "Initial Phase Formation at the Interface of Ni, Pd, or Pt and Si," 1984, pp. unknown, Mat. Res. Soc. Symp. Proc., Vol. 25				
		Nemanich et al., "Structure and Growth of the Interface of Pd on a-SiH," June 15, 1981, pp. 6828-6831, The American Physical Society Physics Review, Vol. 22, No. 12				
		Hemple et al., "Needle-Like Crystallization of Ni Doped Amorphous Silicon Thin Film," 1993, pp. 921-924, Solid State Communications, Vol. 85, No. 11				
		Kuo, "Thin Film Transistor Technologies," Vol. 94-35, pp. 116-122, The Electrochemical Society Proceedings				
		Author Unknown, "Thermo Auto-Chrome Full Color Recording Technology," May 31, 1995, pp. Unknown, Technology Information Association				
:		Wolf et al., "Thermal Oxidation of Single Crystal Silicon," 1986, pp. 207-211, Silicon Processing for the VLSI Era				
4		Erokhin et al., "Spatially Confined Nickel Disilicide Formation at 400C on Ion Implantation Preamorphized Silicon," Dec. 6, 1993, pp. 3173-3175, Appl. Phys. Lett. 63 (23)				
		Dvurechenskii et al., "Transport Phenomena in Amorphous Silicon Doped by Ion Implantation of 3d Metals," 1986, pp. 635-640, Akademikian Lavrentev Prospekt 13, 630090 Novosibirsk 90, USSR				
		Batstone et al., "Microscopic Processes in Crystallization," January 1, 1994, pp. 257-268, Solid State Phenomena, Vol. 37-38				
		Cammarata et al., "Silicide Precipitation and Silicon Crystallization in Nickel Implanted Amorphous Silicon Thin Films," Oct 10, 1990, pp. 2133-2138, J. Mater. Res. Vol. 5, No. 10				
V		Hayzelden et al., "Silicide Formation and Silicide Mediated Crystallization of Nickel- Implanted Amorphous Silicon Thin Films," May 15, 1993, pp. 8279-8289, J. Appl. Phys. 73(12)				

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	U.S. PATENT DOCUMENTS									
Examiner Initials	Cite No.1	U.S. Patent	U.S. Patent Document Name of Patentee or Applicant of Cited	Name of Patentee or Applicant of Cited	Date of Publication of Cit Document	ed Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear				
α		Number	Kind Code ¹ (if known)	Document	MM-DD-YYYY					
1		5,705,829		Miyanaga et al.	01/06/98	7				
		5,712,191		Nakajima et al.	01/27/98					
		5,756,364		Tanaka et al.	05/26/98					
		5,619,044		Makita et al.	04/08/97					
		5,530,266		Yonehara et al.	06/25/96					
		5,550,070		Funai et al.	08/27/96					
		5,693,959		Inoue et al.	12/02/97					

		OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS	
Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.)., date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ³
		Kuznetsov et al., "Silicide Precipitate Formation and Solid Phase Re-Growth of Ni- Implanted Amorphous Silicon," April 5-8, 1993, pp. 191-194, Inst. Phys. Conf. Ser. No. 134.4: Proceedings of Royal Microscipical Society Conf.	
		Liu et al., "Polycrystalline Silicon Thin Film Transistors on Corning 7059 Glass Substrates Using Short Time, Low-Temperature Processing," May 17, 1993, pp. 2554- 2556, Appl. Phys. Lett 62(20)	
		Liu et al., "Selective Area Crystallization of Amorphous Silicon Films by Low- Temperature Rapid Thermal Annealing," August 14, 1989, pp. 660-662, Appl. Phys. Lett 55(7)	
		Spaepen et al., Metal-Enhanced Growth of Silicon, 1992, pp. 483-499, Crucial Issues in Semiconductor Materials & Processing Technologies	
		<i>y</i> .	

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	for form 1449A/PTO			Complete if Known		
INFORMATION DISCLOSURE				Application Number	Based on 10/214,691	
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		Number Kind Code ³ (if known)			
18		5,403,772	Zhang et al.	04/04/95	
1		5,426,064	Zhang et al.	06/20/95	
		5,481,121	Zhang et al.	01/02/96	
		5,488,000	Zhang et al.	01/30/96	1 /
		5,492,843	Adachi et al.	02/20/96	
		5,501,989	Takayama et al.	03/26/96	
		5,508,533	Takemura	04/16/96	
		5,529,937	Zhang et al.	06/25/96	
,		5,534,716	Takemura	07/09/96	
		5,543,352	Ohtani et al.	08/06/96	\
		5,563,426	Zhang et al.	10/08/96	
		5,569,610	Zhang et al.	10/29/96	
 		5,569,936	Zhang et al.	10/29/96	
		5,580,792	Zhang et al.	12/03/96	, , , , , , , , , , , , , , , , , , , ,
		5,585,291	Ohtani et al.	12/17/96	/
		5,589,694	Takayama et al.	12/31/96	
		5,595,923	Zhang et al.	01/21/97	/
		5,595,944	Zhang et al.	01/21/97	/
		5,604,360	Zhang et al.	02/18/97	1
		5,605,846	Ohtani et al.	02/25/97	
		5,606,179	Yamazaki et al.	02/25/97	
	İ	5,608,232	Yamazaki et al.	03/04/97	
		5,612,250	Ohtani et al.	03/18/97	
		5,614,426	Funada et al.	03/25/97	· ·
		5,614,733	Zhang et al.	03/25/97	
		5,616,506	Takemura	04/01/97	
-		5,620,910	Teramoto	04/15/97	1
		5,621,224	Yamazaki et al.	04/15/97	
	-	5,624,851	Takayama et al.	04/29/97	
	<u> </u>	5,637,515	Takemura	06/10/97	
	<u> </u>	5,639,698	Yamazaki et al.	06/17/97	
		5,643,826	Ohtani et al.	07/01/97	1 /
	<u> </u>	5,646,424	Zhang et al.	07/08/97	1/
		5,654,203	Ohtani et al.	08/05/97	į
		5,656,825	Kusumoto et al.	08/12/97	
		5,663,077	Adachi et al.	09/02/97	
		5,677,549	Takayama et al.	10/14/97	
		5,696,386	Yamazaki	12/09/97	
/		5,696,388	Funada et al.	12/09/97	<u> </u>
/		5,700,333	Yamazaki et al.	12/23/97	<u> </u>

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	No.	Number Kind Code (if known)	Document	MM-DD-YYYY		
PR		5,932,893	Miyanaga et al.	08/03/99		
		4,759,610	Yanagisawa	07/26/88	,	
		5,535,471	Guldi	07/16/96		
		5,661,056	Takeuchi	08/26/97		
		4,140,548	Zimmer	02/20/79		
		5,210,050	Yamazaki et al.	05/11/93		
		5,298,075	Lagendijk et al.	03/29/94		
		5,306,651	Masumo et al.	04/26/94		
	l	5,313,076	Yamazaki et al.	05/17/94		
		5,365,080	Yamazaki et al.	11/15/94		
		5,372,860	Fehlner et al.	12/13/94		
Ī		5,591,988	Arai et al.	01/07/97	/	
	Ì	5,893,730	Yamazaki et al.	04/13/99		
1,		5,913,111	Kataoka et al.	06/15/99		
1/		5,953,597	Kusumoto et al.	09/14/99		
1		6,011,275	Ohtani et al.	01/04/00		
7		6,133,073	Yamazaki et al.	10/17/00		
		OTHER I	PRIOR ART + NON PATENT LITERAT	TURE DOCUMENTS		
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Pa		Wolf, Silicon Proces	sing for the VLSI Era, Volume	2, Chapter 4, page 2	74 (1990).	
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U.S. PATENT DOCUMENTS										
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10		6,225,152	B1	Yamazaki et al.	05/01/01					
		6,288,412	B1	Hamada et al.	09/11/01					
		6,323,072	B1	Yamazaki et al.	11/27/01					
1/		6,331,718	B1	Yamazaki et al.	12/18/01					
			 							
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FA		6,162,704			Yamazaki et al.			12/19/2000				
1	1		94,441		Yamazaki			09/25/2001				
	1		161,943		Yamazaki et al.			10/08/2002				
			20,711			nazaki		09/16/2003				
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		JP	08-045840		\dagger		02	2/16/1996			Equiv. Abst. & U.S.	
	-	JP	08-097169		+		04	1/12/1996			Equiv. Abst. & U.S.	
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		JP	07-045519				02	2/14/1995			Abst. & U.S. Equiv.	
		JP	07-231100				08	3/29/1995			Abst. & U.S. Equiv.	
/		JP	07-094757				04	4/07/1995		1	Abst. & U.S. Equiv.	
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